



FEATURES

- Submicron position resolution
- Stable response after exposure to UV/EUV
- 5 mm x 5 mm active area
- TO-8 windowless package

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area			25		mm ²
Responsivity, \mathcal{R}	@ 13 nm		0.2		A/W
Responsivity, \mathcal{R}	@ 254 nm		0.02		A/W
Dark Current I_{dr}	$V_R = 30\text{ V}$		10	50	nA
Reverse Breakdown Voltage, V_R	$I_R = 1\ \mu\text{A}$	50			Volts
Capacitance, C	$V_R = 30\text{ V}$		40	60	pF
Rise Time	$V_R = 30\text{ V}, R_L = 50\ \Omega$		200		nsec
Shunt Resistance	$V_f = \pm 10\text{ mV}$	5			MOhms
Inter Electrode Resistance		5,000	10,000	15,000	Ohms
Temp Coefficient of ID			1.15		Times/°C
Position Non-Linearity ¹			1	2	±%

¹Valid within 80% of length

THERMAL PARAMETERS

STORAGE AND OPERATING TEMPERATURE RANGE	
Ambient	-10°C to 40°C
Nitrogen or Vacuum	-20°C to 80°C
Maximum Junction Temperature	70°C
Lead Soldering Temperature ¹	260°C

¹0.08" from case for 10 seconds

